

**P-CHANNEL MOS FIELD EFFECT TRANSISTOR
FOR SWITCHING**

DESCRIPTION

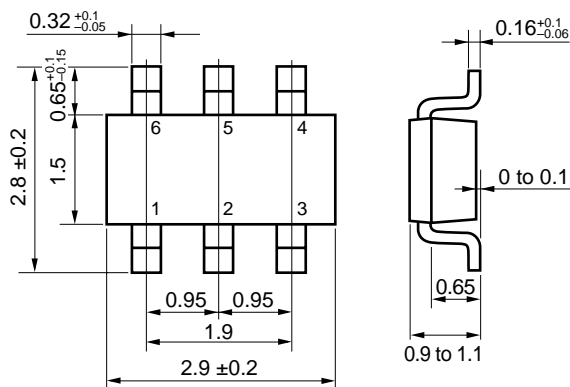
The μ PA1911A is a switching device which can be driven directly by a 2.5 V power source.

The μ PA1911A features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- Can be driven by a 2.5 V power source
- Low on-state resistance
 $R_{DS(on)1} = 115 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -1.5 \text{ A)}$
 $R_{DS(on)2} = 120 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.0 \text{ V, } I_D = -1.5 \text{ A)}$
 $R_{DS(on)3} = 190 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -1.0 \text{ A)}$

PACKAGE DRAWING (Unit : mm)



1, 2, 5, 6 : Drain
3 : Gate
4 : Source

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1911ATE ^{Note}	SC-95 (Mini Mold Thin Type)

Note Marking: TK

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

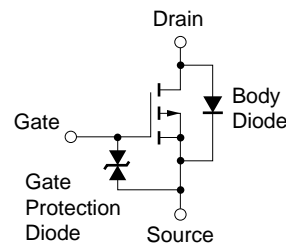
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±12	V
Drain Current (DC)	I _{D(DC)}	±2.5	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±10	A
Total Power Dissipation	P _{T1}	0.2	W
Total Power Dissipation (T _A = 25°C) ^{Note2}	P _{T2}	2	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

- Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%
2. Mounted on FR-4 board, t ≤ 5 sec.

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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 Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

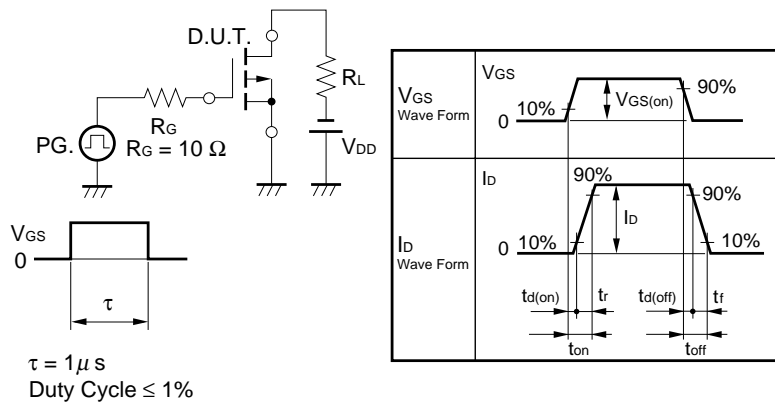
EQUIVALENT CIRCUIT



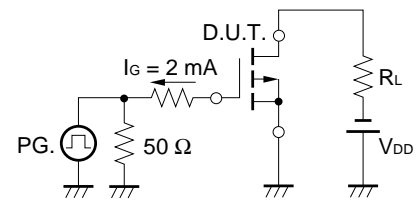
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12 V, V _{DS} = 0 V			± 10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-0.5	-1.0	-1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -1.5 A	1	5.4		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -1.5 A		82	115	mΩ
	R _{DS(on)2}	V _{GS} = -4.0 V, I _D = -1.5 A		86	120	mΩ
	R _{DS(on)3}	V _{GS} = -2.5 V, I _D = -1.0 A		122	190	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		370		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		110		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		40		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V, I _D = -1.5 A		130		ns
Rise Time	t _r	V _{GS} = -4.0 V		230		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		470		ns
Fall Time	t _f			380		ns
Total Gate Charge	Q _G	V _{DD} = -10 V		2.3		nC
Gate to Source Charge	Q _{GS}	I _D = -2.5 A		1.0		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = -4.0 V		1.0		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 2.5 A, V _{GS} = 0 V		0.84		V
Reverse Recovery Time	t _{rr}	I _F = 2.5 A, V _{GS} = 0 V		14		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 10 A/μs		1.4		nC

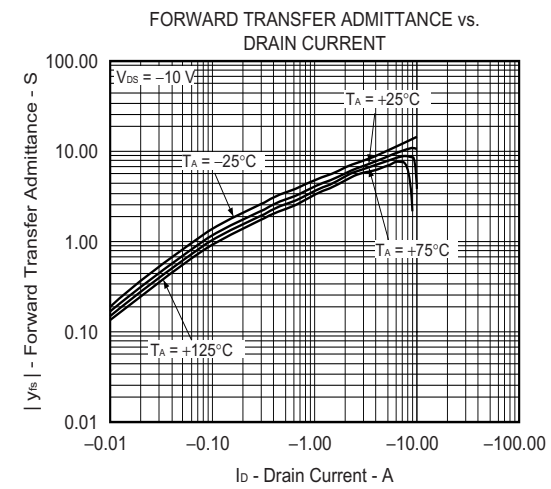
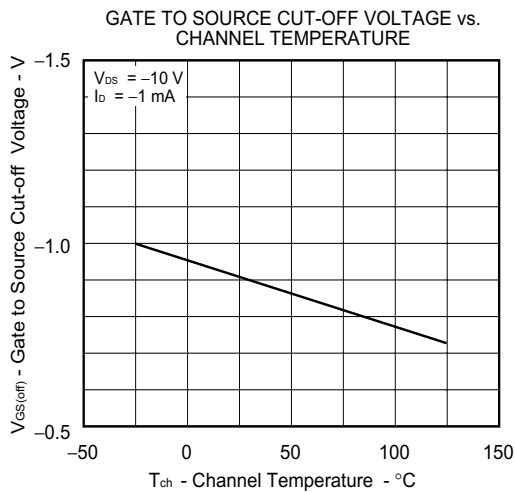
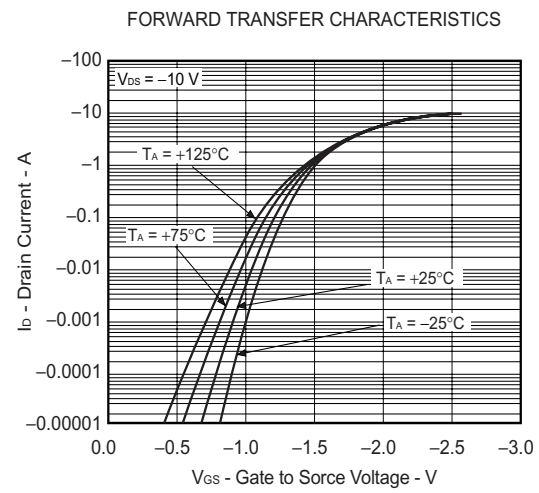
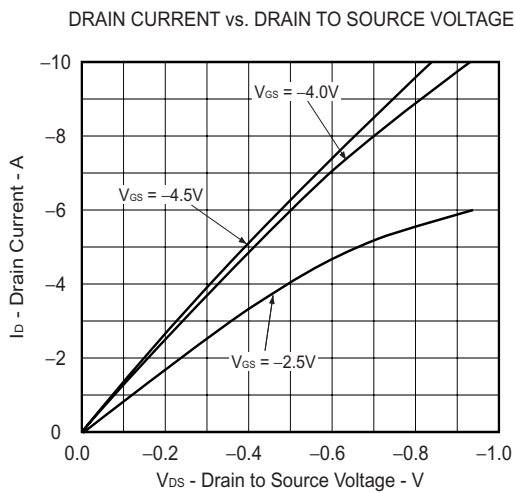
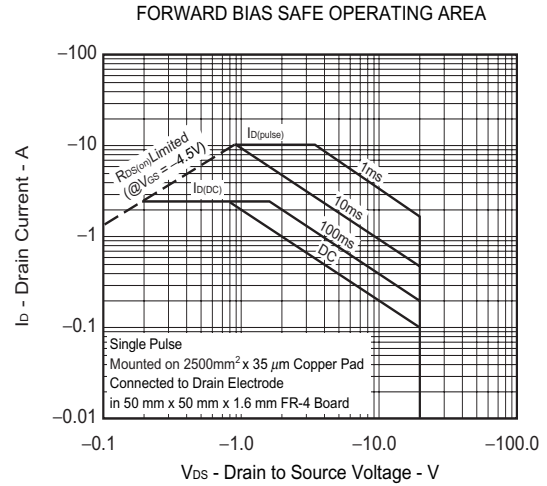
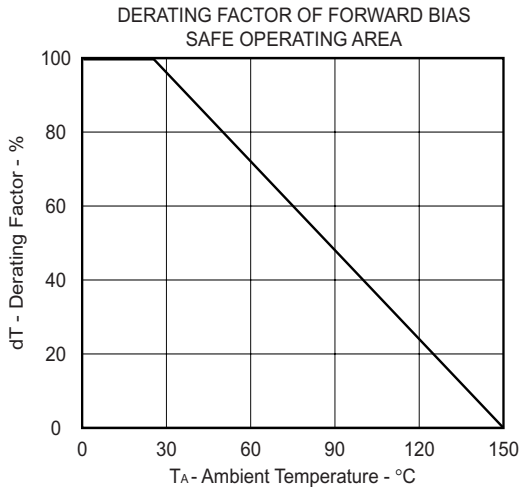
TEST CIRCUIT 1 SWITCHING TIME

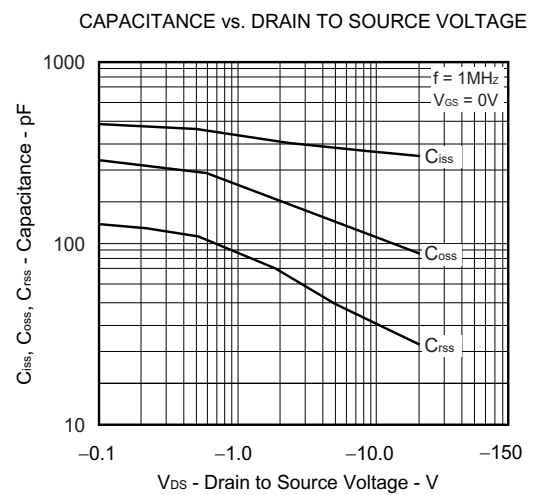
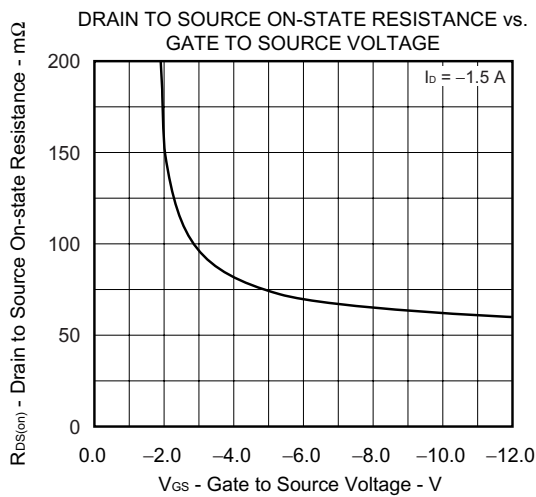
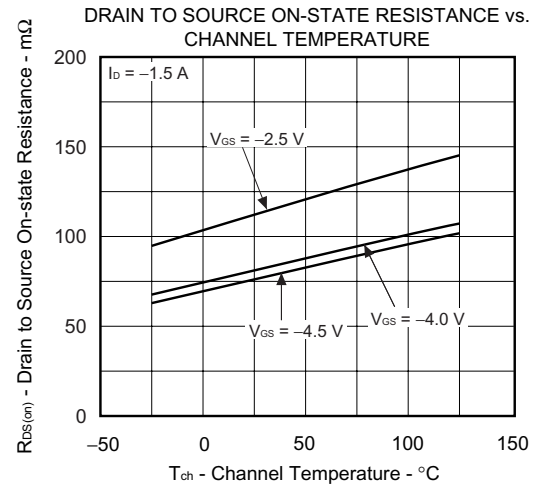
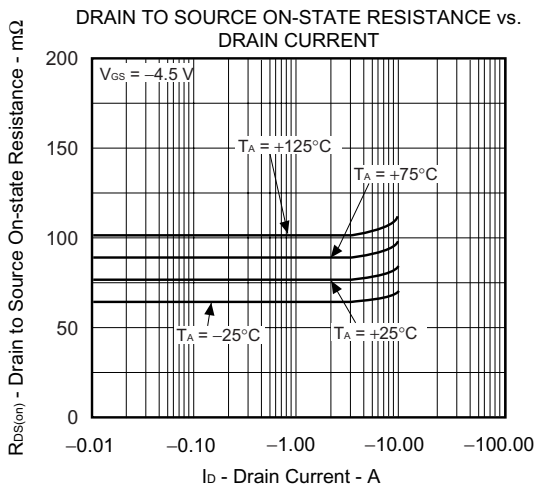
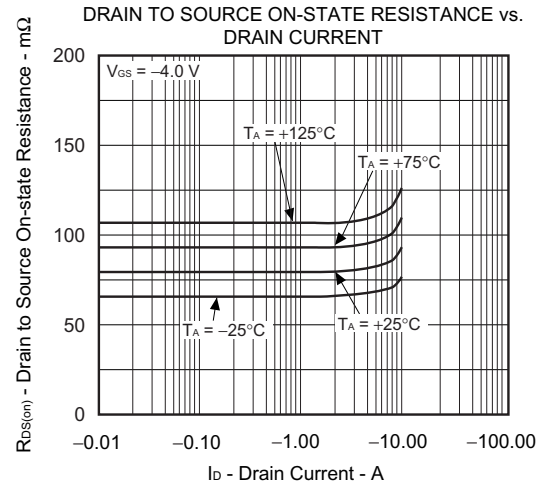
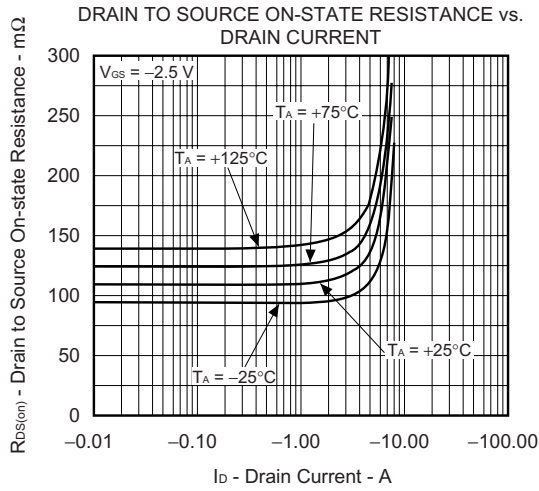


TEST CIRCUIT 2 GATE CHARGE

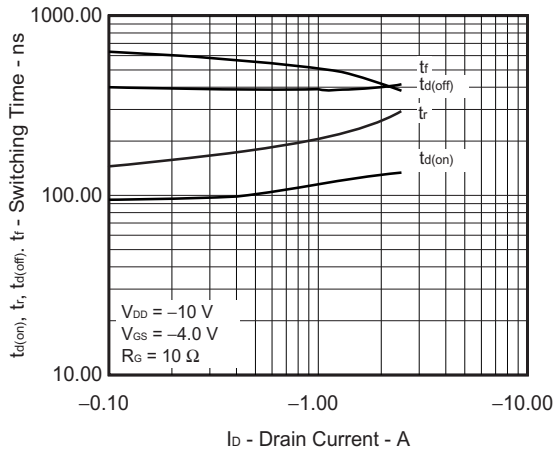


TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

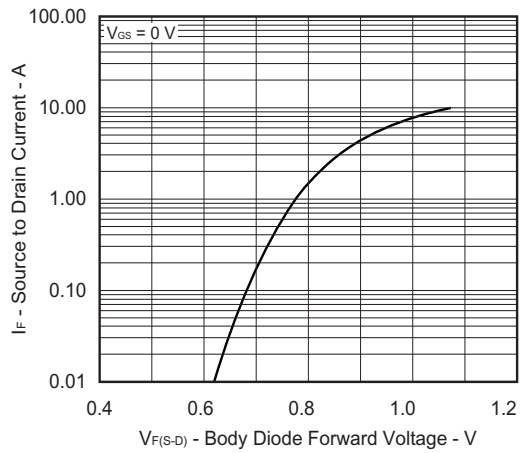




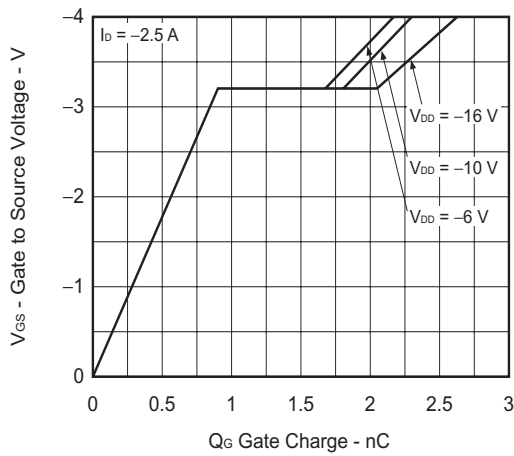
SWITCHING CHARACTERISTICS



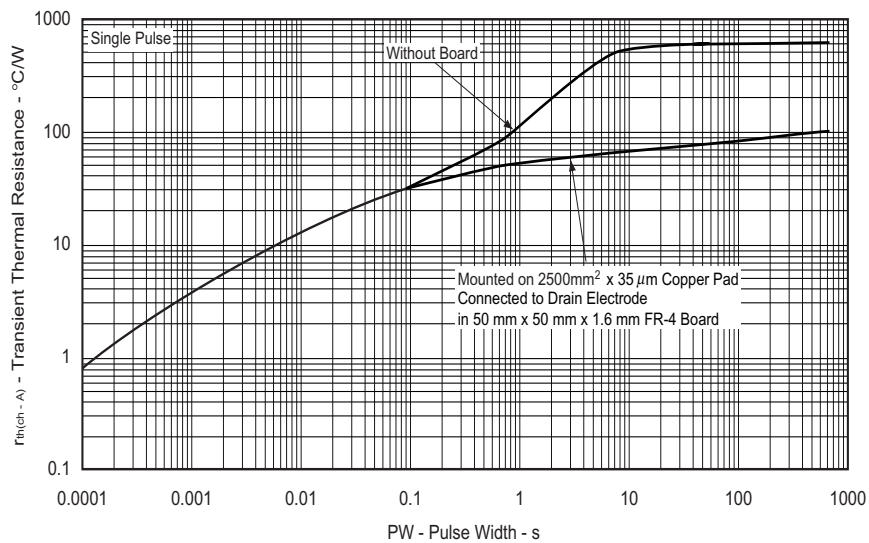
SOURCE TO DRAIN FORWARD VOLTAGE



DYNAMIC INPUT CHARACTERISTICS



TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



[MEMO]

[MEMO]

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